

60V N-Channel Enhancement Mode MOSFET

Description

The AP240N06P/T uses advanced **SGT II** technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

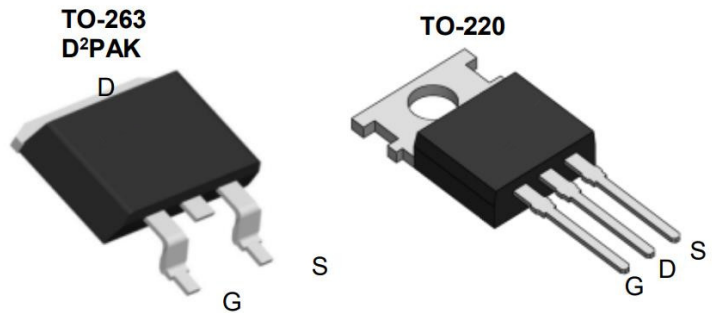
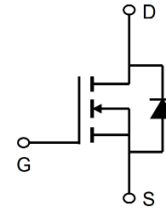
$V_{DS} = 60V$ $I_D = 240A$

$R_{DS(ON)} < 3.2m\Omega$ @ $V_{GS}=10V$ (Type: **2.4mΩ**)

Application

Battery protection

UPS



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP240N06P	TO-220-3L	AP240N06P XXX YYYY	1000
AP240N06T	TO-263-3L	AP240N06T XXX YYYY	800

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ^{1,6}	240	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ^{1,6}	166	A
IDM	Pulsed Drain Current ²	820	A
EAS	Single Pulse Avalanche Energy ³	560	mJ
IAS	Avalanche Current	55	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	168	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	0.89	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	1.5	$^\circ\text{C/W}$



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Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	60	-	-	V
IGSS	Gate-body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
IDSS T _J =25°C	Zero Gate Voltage Drain Current	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μA
IDSS T _J =100°C	Zero Gate Voltage Drain Current		-	-	100	
VGS(th)	Gate-Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	2.8	4.0	V
RDS(on)	Drain-Source On-Resistance ⁴	V _{GS} = 10V, I _D = 20A	-	2.4	3.2	mΩ
gfs	Forward Transconductance ⁴	V _{DS} = 5V, I _D = 20A	-	78	-	S
Ciss	Input Capacitance	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	-	5245	-	pF
Coss	Output Capacitance		-	1090	-	
Crss	Reverse Transfer Capacitance		-	25	-	
RG	Gate Resistance	f = 1MHz	-	2.2	-	Ω
Q _g	Total Gate Charge	V _{GS} = 10V, V _{DS} = 30V, I _D = 20A	-	72.5	-	nC
Q _{gs}	Gate-Source Charge		-	19.5	-	
Q _{gd}	Gate-Drain Charge		-	14	-	
td(on)	Turn-on Delay Time	V _{GS} = 10V, V _{DD} = 30V, R _G = 3Ω, I _D = 20A	-	26.5	-	ns
t _r	Rise Time		-	15	-	
td(off)	Turn-off Delay Time		-	73	-	
t _f	Fall Time		-	18	-	
trr	Body Diode Reverse Recovery Time	I _F = 20A, dI/dt = 100A/μs	-	25	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	90	-	nC
VSD	Diode Forward Voltage ⁴	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
IS	Continuous Source Current T _C = 25°C	-	-	-	125	A

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The power dissipation is limited by 175°C junction temperature
- 4、EAS condition: T_J=25°C, V_{DD}=48V, V_G=10V, R_G=25Ω, L=0.1mH, I_{AS}= 55A
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

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Typical Characteristics

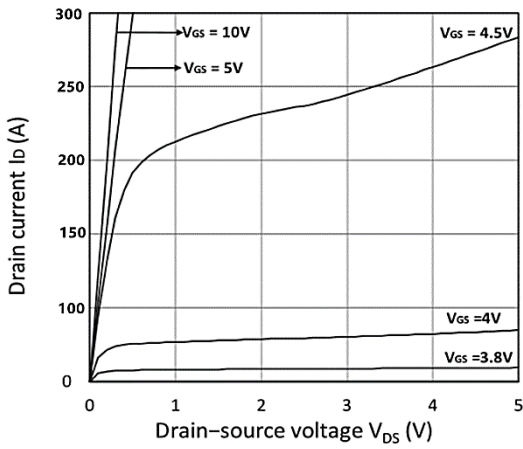


Figure 1. Output Characteristics

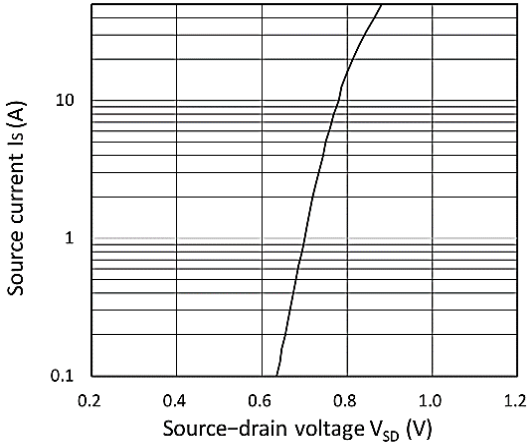


Figure 3. Forward Characteristics of Reverse

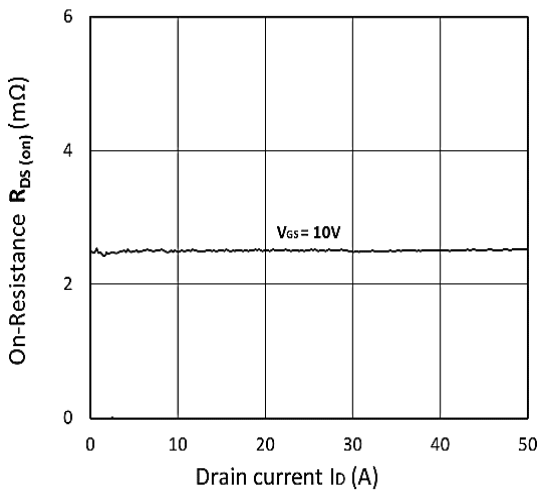


Figure 5. R DS(ON) vs. ID

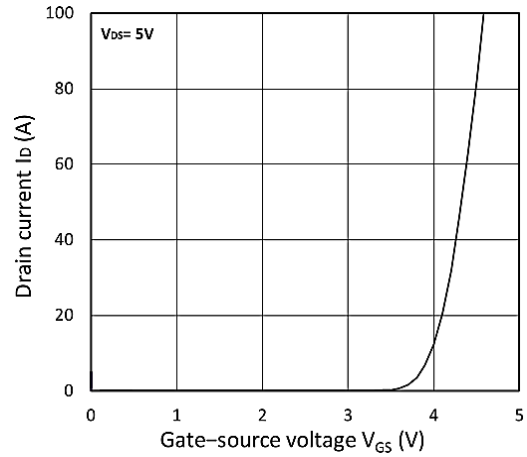


Figure 2. Transfer Characteristics

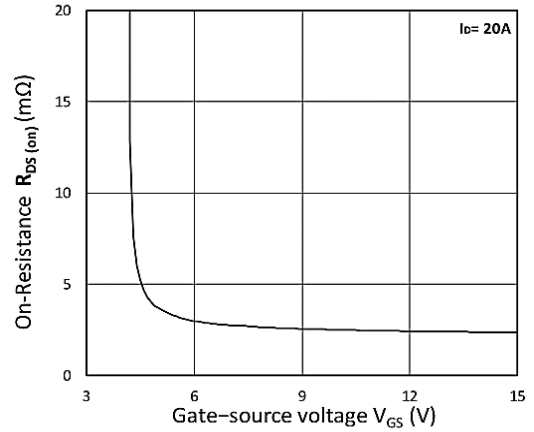


Figure 4. RDS(ON) vs. VGS

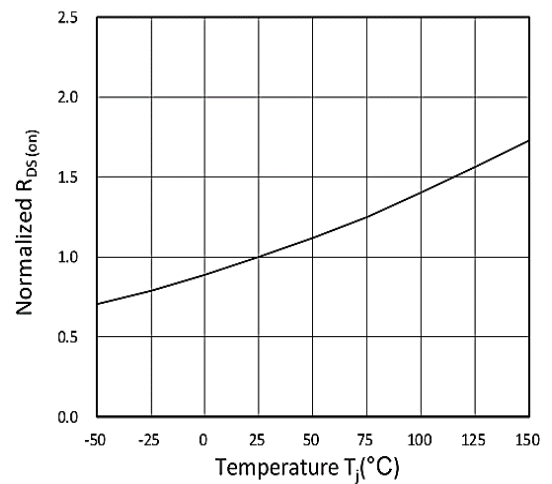


Figure 6. Normalized R DS(on) vs. Temperature

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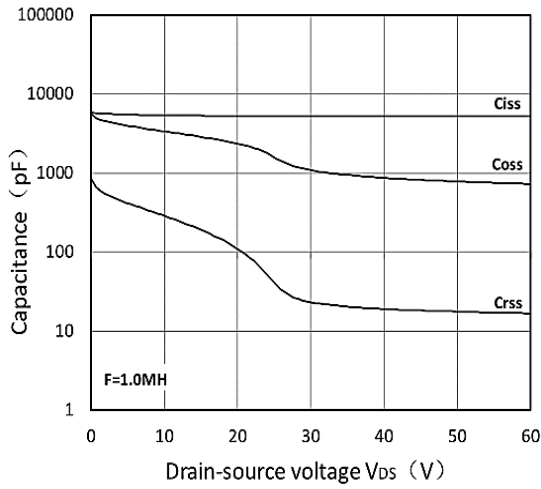


Figure 7. Capacitance Characteristics

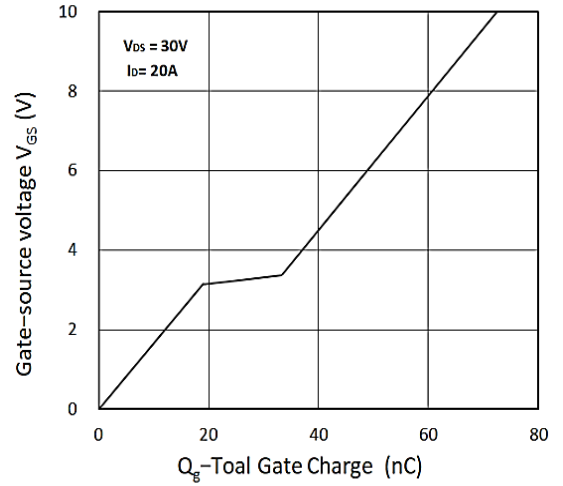


Figure 8. Gate Charge Characteristics

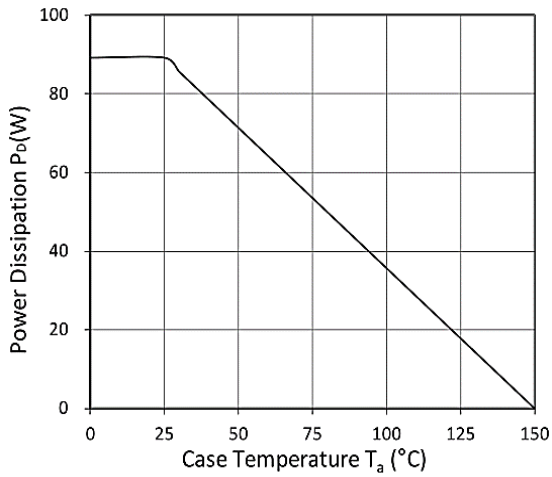


Figure 9. Power Dissipation

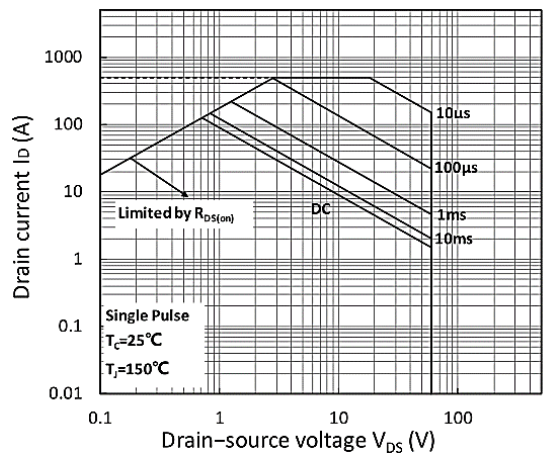


Figure 10. Safe Operating Area

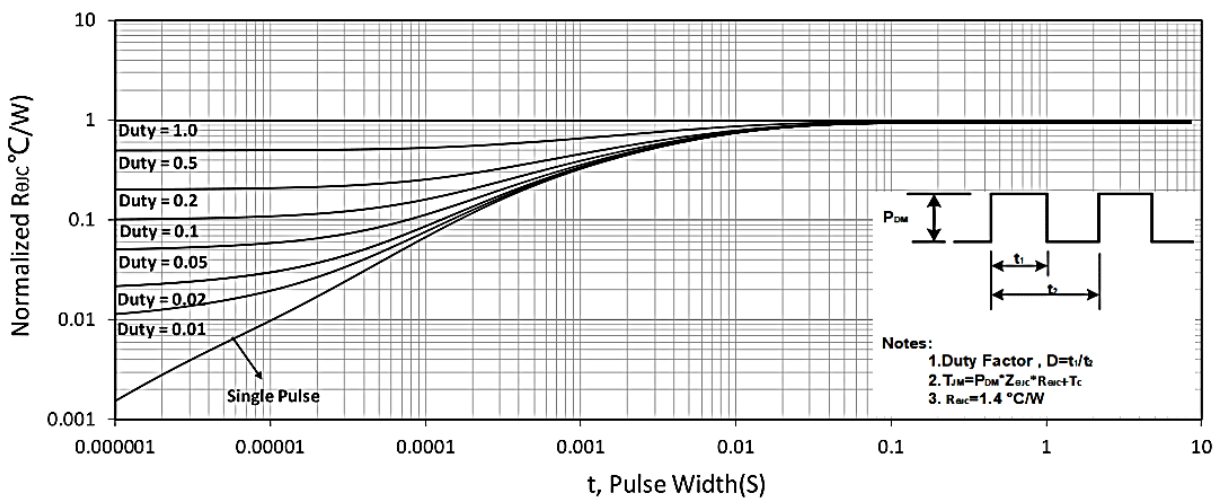
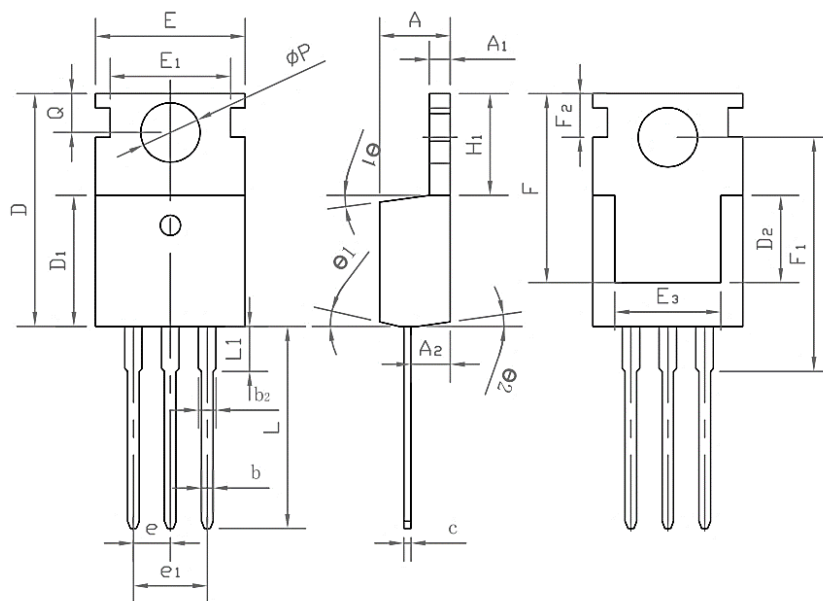


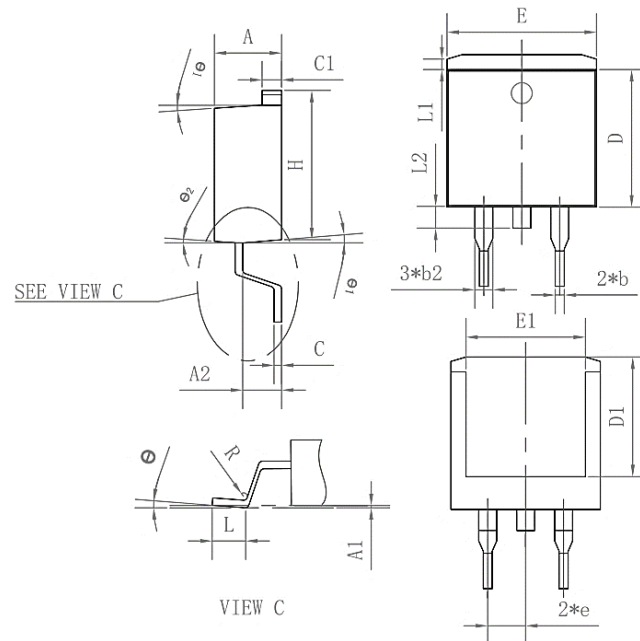
Figure 11. Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-TO-220-3L-SLK


Symbol	Common		
	mm		
	Mim	Nom	Max
A	4.27	4.57	4.87
A1	1.15	1.30	1.45
A2	2.10	2.40	2.70
b	0.70	0.80	1.00
b2	1.17	1.27	1.50
D	0.40	0.50	0.65
D1	8.80	9.10	9.40
D2	5.70	6.70	7.00
E	9.70	10.00	10.30
E1	-	8.70	-
E2	9.63	10.00	10.35
E3	7.00	8.00	8.40
e		0.37	
e1		0.10	
H1	6.00	6.50	6.85
L	12.75	13.50	13.90
L1	-	3.10	3.40
Φp	3.45	3.60	3.75
Q	2.60	2.80	3.00
θ_1	4°	7°	10°
θ_2	0°	3°	6°
F	13.30	13.50	13.70
F1	15.50	15.90	16.30
F2	2.80	3.00	3.20

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Package Mechanical Data-TO-263-3L-SLK



Symbol	Common		
	mm		
	Mim	Nom	Max
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.70
b	0.70	0.80	1.00
b2	1.25	1.36	1.50
C	0.45	0.50	0.65
C1	1.29	1.30	9.40
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70
e	-	2.54	-
L	2.34	2.54	2.74
L1	1.00	1.10	1.20
L2	1.30	1.40	1.50
R	0.24	0.25	0.26
θ	0°	4°	8°
θ1	4°	7°	10°
θ2	0°	3°	6°